

## LOW DROP POWER SCHOTTKY RECTIFIER

### MAIN PRODUCT CHARACTERISTICS

|                            |               |
|----------------------------|---------------|
| <b>I<sub>F(AV)</sub></b>   | <b>10 A</b>   |
| <b>V<sub>RRM</sub></b>     | <b>25 V</b>   |
| <b>T<sub>j (max)</sub></b> | <b>150 °C</b> |
| <b>V<sub>F (max)</sub></b> | <b>0.35 V</b> |

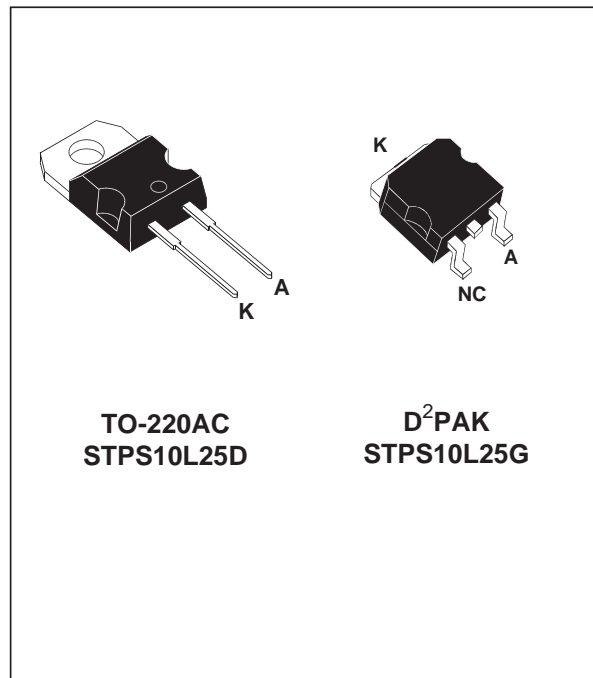
### FEATURES AND BENEFITS

- VERY LOW FORWARD VOLTAGE DROP FOR LESS POWER DISSIPATION
- OPTIMIZED CONDUCTION / REVERSE LOSSES TRADE-OFF WHICH MEANS THE HIGHEST EFFICIENCY IN THE APPLICATIONS
- AVALANCHE CAPABILITY SPECIFIED

### DESCRIPTION

Single Schottky rectifier suited to Switched Mode Power Supplies and high frequency DC to DC converters.

This device is especially intended for use as a rectifier at the secondary of 3.3V SMPS units.



**TO-220AC  
STPS10L25D**

**D<sup>2</sup>PAK  
STPS10L25G**

### ABSOLUTE RATINGS (limiting values)

| Symbol              | Parameter                                |  | Value         | Unit |
|---------------------|--|--|---------------|------|
| V <sub>RRM</sub>    | Repetitive peak reverse voltage          |  | 25            | V    |
| I <sub>F(RMS)</sub> | RMS forward current                      |  | 30            | A    |
| I <sub>F(AV)</sub>  | Average forward current                  | T <sub>c</sub> = 140°C δ = 0.5             | 10            | A    |
| I <sub>FSM</sub>    | Surge non repetitive forward current     | t <sub>p</sub> = 10 ms Sinusoidal          | 200           | A    |
| I <sub>RRM</sub>    | Repetitive peak reverse current          | t <sub>p</sub> =2 μs square F=1kHz         | 1             | A    |
| I <sub>RSM</sub>    | Non repetitive peak reverse current      | t <sub>p</sub> = 100 μs square             | 3             | A    |
| P <sub>ARM</sub>    | Repetitive peak avalanche power          | t <sub>p</sub> = 1μs T <sub>j</sub> = 25°C | 5500          | W    |
| T <sub>stg</sub>    | Storage temperature range                |  | - 65 to + 150 | °C   |
| T <sub>j</sub>      | Maximum operating junction temperature * |  | 150           | °C   |
| dV/dt               | Critical rate of rise of reverse voltage |  | 10000         | V/μs |

\* :  $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j-a)}$  thermal runaway condition for a diode on its own heatsink

# STPS10L25D/G

## THERMAL RESISTANCE

| Symbol        | Parameter        | Value | Unit                        |
|---------------|------------------|-------|-----------------------------|
| $R_{th(j-c)}$ | Junction to case | 1.5   | $^{\circ}\text{C}/\text{W}$ |

## STATIC ELECTRICAL CHARACTERISTICS

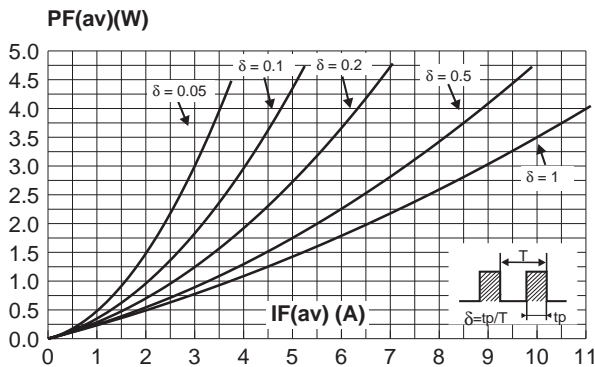
| Symbol  | Tests Conditions        | Tests Conditions            | Min.                | Typ. | Max. | Unit |               |
|---------|-------------------------|-----------------------------|---------------------|------|------|------|---------------|
| $I_R^*$ | Reverse leakage current | $T_j = 25^{\circ}\text{C}$  | $V_R = V_{RRM}$     |      |      | 800  | $\mu\text{A}$ |
|         |                         | $T_j = 125^{\circ}\text{C}$ |                     |      | 135  | 260  | $\text{mA}$   |
| $V_F^*$ | Forward voltage drop    | $T_j = 25^{\circ}\text{C}$  | $I_F = 10\text{ A}$ |      |      | 0.46 | V             |
|         |                         | $T_j = 125^{\circ}\text{C}$ | $I_F = 10\text{ A}$ |      | 0.30 | 0.35 |               |
|         |                         | $T_j = 25^{\circ}\text{C}$  | $I_F = 20\text{ A}$ |      |      | 0.55 |               |
|         |                         | $T_j = 125^{\circ}\text{X}$ | $I_F = 20\text{ A}$ |      | 0.41 | 0.48 |               |

Pulse test: \*  $t_p = 380\ \mu\text{s}$ ,  $\delta < 2\%$

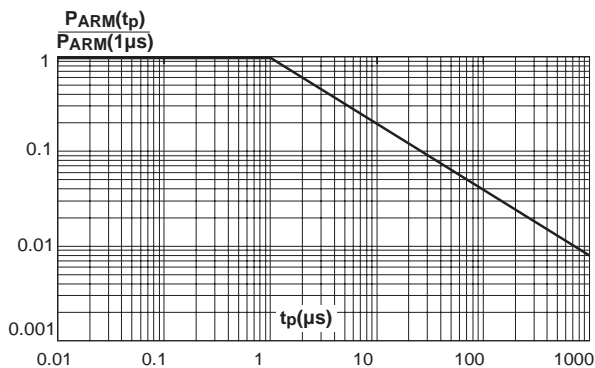
To evaluate the maximum conduction losses use the following equation :

$$P = 0.22 \times I_{F(AV)} + 0.013 I_{F(RMS)}^2$$

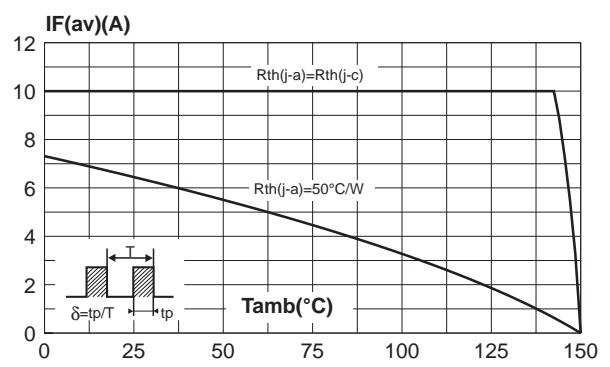
**Fig. 1:** Average forward power dissipation versus average forward current.



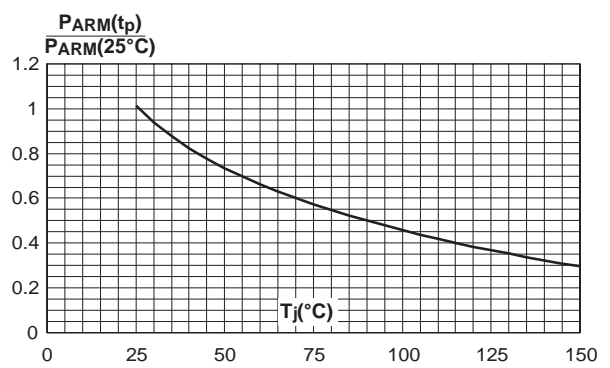
**Fig. 3:** Normalized avalanche power derating versus pulse duration.



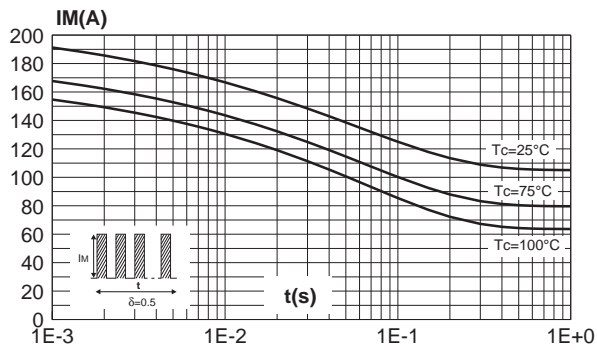
**Fig. 2:** Average forward current versus ambient temperature ( $\delta = 0.5$ ).



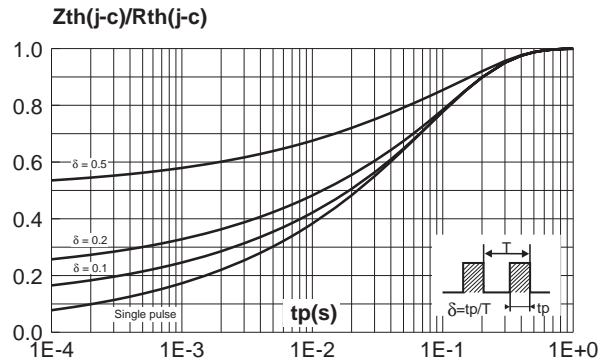
**Fig. 4:** Normalized avalanche power derating versus junction temperature.



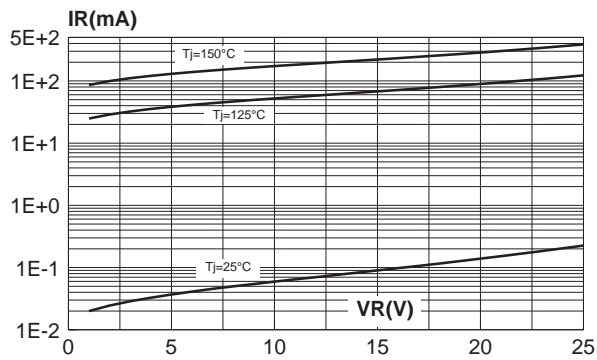
**Fig. 5:** Non repetitive surge peak forward current versus overload duration (maximum values).



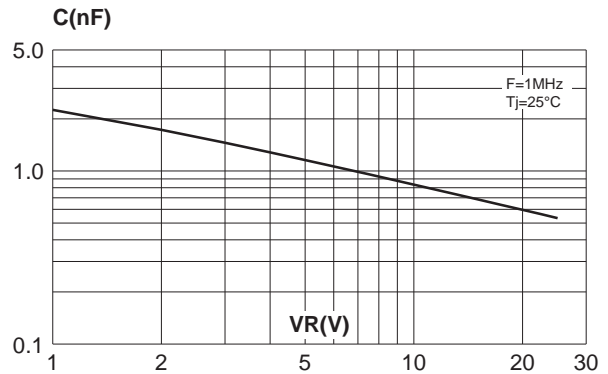
**Fig. 6:** Relative variation of thermal impedance junction to case versus pulse duration.



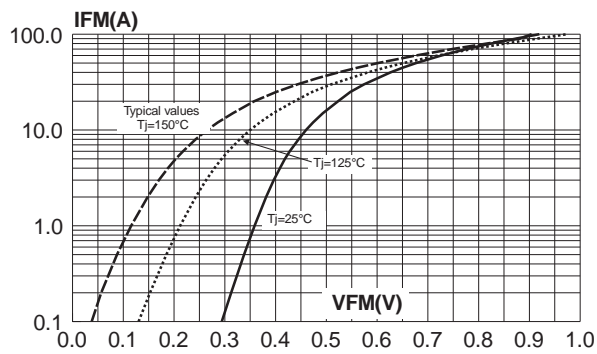
**Fig. 7:** Reverse leakage current versus reverse voltage applied (typical values).



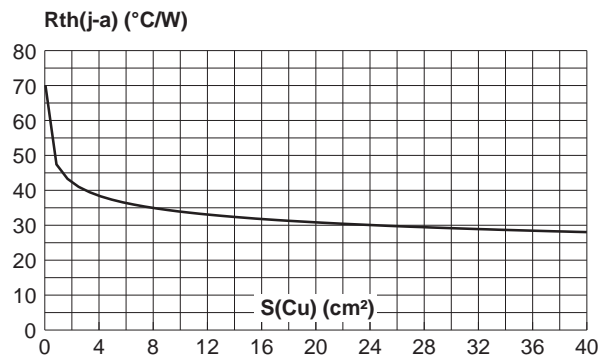
**Fig. 8:** Junction capacitance versus reverse voltage applied (typical values).



**Fig. 9:** Forward voltage drop versus forward current (maximum values).

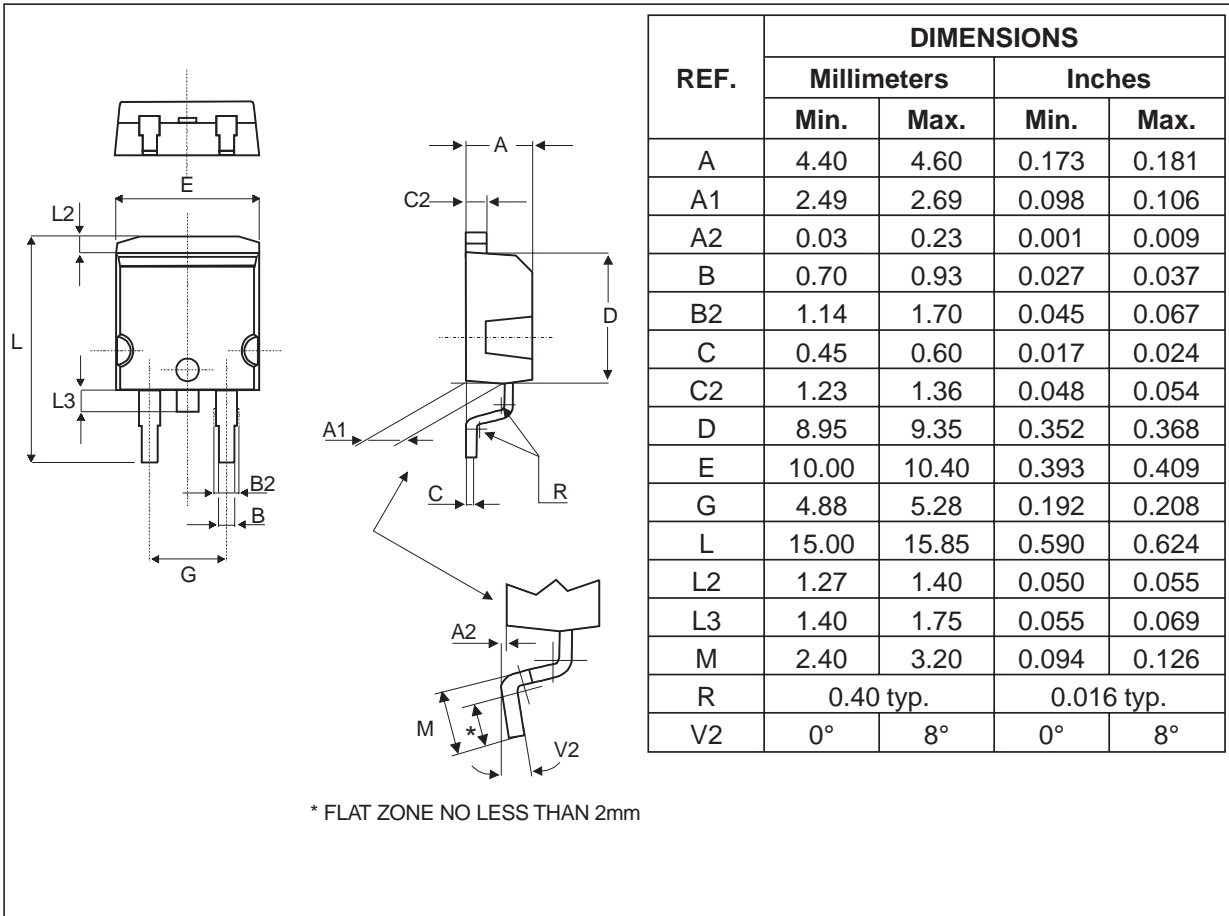


**Fig. 10:** Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4, copper thickness : 35 μm). (STPS10L25G only)

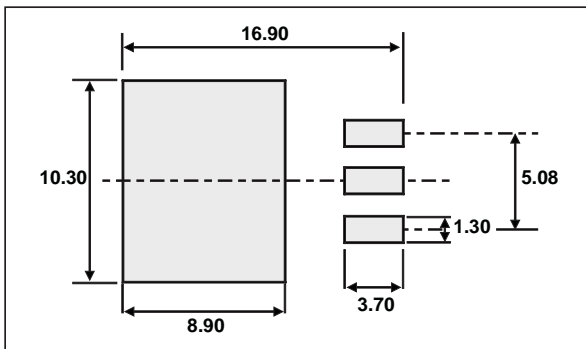


**STPS10L25D/G**

**PACKAGE MECHANICAL DATA**  
D<sup>2</sup>PAK



**FOOT PRINT DIMENSIONS (in millimeters)**



- Cooling method: by conduction (method C)

**PACKAGE MECHANICAL DATA**  
 TO-220AC

| REF.    | DIMENSIONS  |       |            |       |
|---------|-------------|-------|------------|-------|
|         | Millimeters |       | Inches     |       |
|         | Min.        | Max.  | Min.       | Max.  |
| A       | 4.40        | 4.60  | 0.173      | 0.181 |
| C       | 1.23        | 1.32  | 0.048      | 0.051 |
| D       | 2.40        | 2.72  | 0.094      | 0.107 |
| E       | 0.49        | 0.70  | 0.019      | 0.027 |
| F       | 0.61        | 0.88  | 0.024      | 0.034 |
| F1      | 1.14        | 1.70  | 0.044      | 0.066 |
| G       | 4.95        | 5.15  | 0.194      | 0.202 |
| H2      | 10.00       | 10.40 | 0.393      | 0.409 |
| L2      | 16.40 typ.  |       | 0.645 typ. |       |
| L4      | 13.00       | 14.00 | 0.511      | 0.551 |
| L5      | 2.65        | 2.95  | 0.104      | 0.116 |
| L6      | 15.25       | 15.75 | 0.600      | 0.620 |
| L7      | 6.20        | 6.60  | 0.244      | 0.259 |
| L9      | 3.50        | 3.93  | 0.137      | 0.154 |
| M       | 2.6 typ.    |       | 0.102 typ. |       |
| Diam. I | 3.75        | 3.85  | 0.147      | 0.151 |

- Cooling method : C
- Recommended torque value : 0.55 m.N
- Maximum torque value : 0.70 m.N

| Ordering type | Marking    | Package            | Weight | Base qty | Delivery mode |
|---------------|------------|--------------------|--------|----------|---------------|
| STPS10L25D    | STPS10L25D | TO-220AC           | 1.86g  | 50       | Tube          |
| STPS10L25G    | STPS10L25G | D <sup>2</sup> PAK | 1.48g  | 50       | Tube          |
| STPS10L25G-TR | STPS10L25G | D <sup>2</sup> PAK | 1.48g  | 1000     | Tape & reel   |

- Epoxy meets UL94,V0

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